

Title (en)
CURRENT CONFINEMENT AND BLOCKING REGION FOR SEMICONDUCTOR DEVICES

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Application
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Priority
US 11491087 A 19871029

Abstract (en)
[origin: EP0314372A2] Improved current confinement and current blocking are achieved in a semiconductor device including a doped (n or p type) semiconductor layer (32) within a region of high resistivity semiconductor material (31,33). In another embodiment, a plurality of doped semiconductor layers are interleaved with a plurality of high resistivity semiconductor layers.

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IPC 8 full level
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Citation (search report)

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